

GJ127

PNP EPITAXIAL PLANAR TRANSISTOR

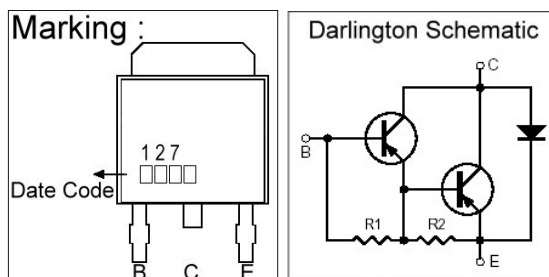
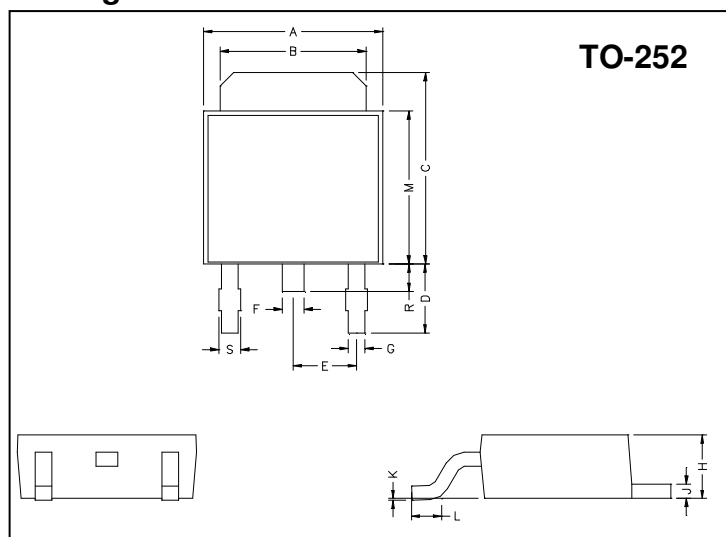
Description

The GJ127 is designed for use in general purposes and low speed switching applications.

Features

- High DC current gain
- Built-in a damper diode at E-C

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings at Ta = 25°C

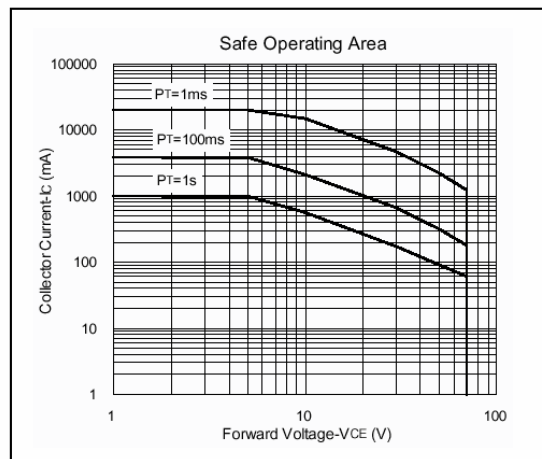
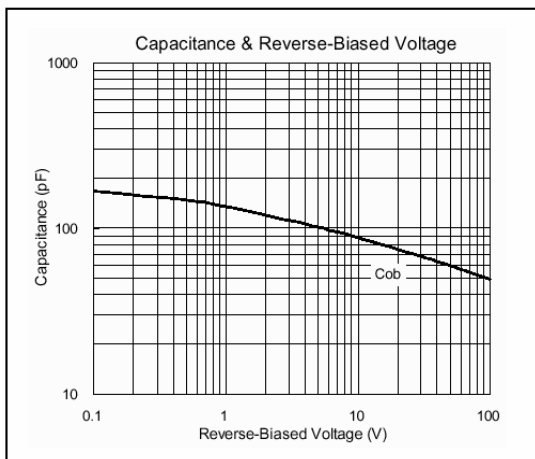
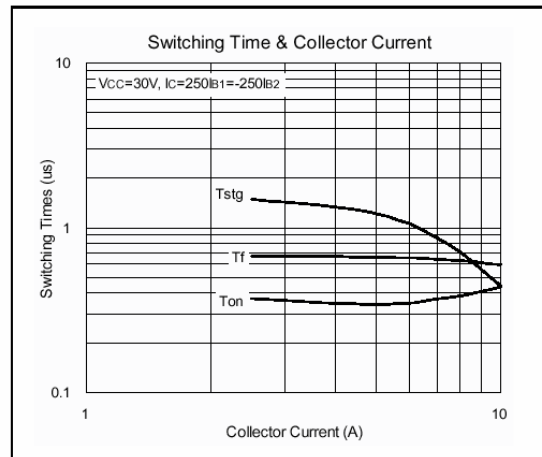
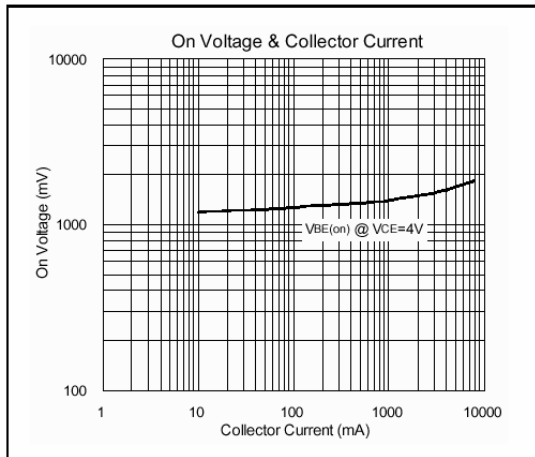
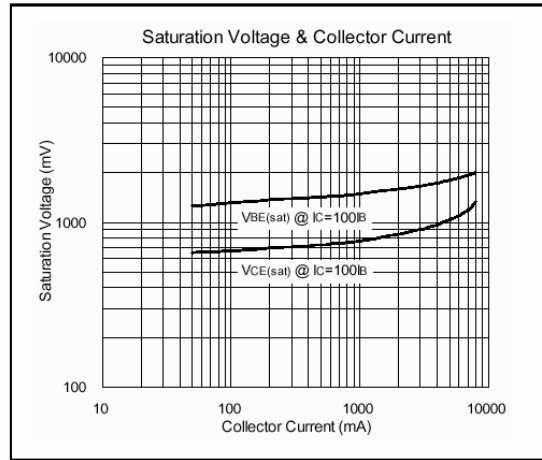
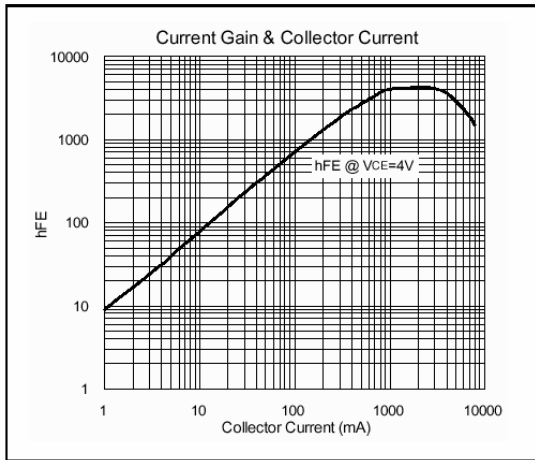
Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	BVCBO	-100	V
Collector to Emitter Voltage	BVCEO	-100	V
Emitter to Base Voltage	BVEBO	-5	V
Collector Current	I _C	-5	A
Total Power Dissipation(T _c =25°C)	PD	20	W

Electrical Characteristics (Rating at 25°C ambient temperature unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-100	-	-	V	I _C =-1mA, I _E =0
BVCEO	-100	-	-	V	I _C =-30mA, I _B =0
BVEBO	-5	-	-	V	I _E =-1mA, I _C =0
I _{CBO}	-	-	-10	μA	V _{CB} =-100V, I _E =0
I _{CEX}	-	-	-10	μA	V _{CE} =-100V, V _{BE(off)} =-1.5V
I _{EBO}	-	-	-2	mA	V _{EB} =-5V, I _C =0
*V _{CE(sat)1}	-	-	-2	V	I _C =-3A, I _B =-12mA
*V _{CE(sat)2}	-	-	-4	V	I _C =-5A, I _B =-20mA
*V _{BE(sat)}	-	-	-4	V	I _C =-5A, I _B =-50mA
*V _{BE(on)}	-	-	-2.8	V	V _{CE} =-3V, I _C =-3A
*h _{FE1}	1	-	-	K	V _{CE} =-3V, I _C =-500mA
*h _{FE2}	1	-	-	K	V _{CE} =-3V, I _C =-3A
C _{ob}	-	-	300	pF	V _{CB} =-10V, f=0.1MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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